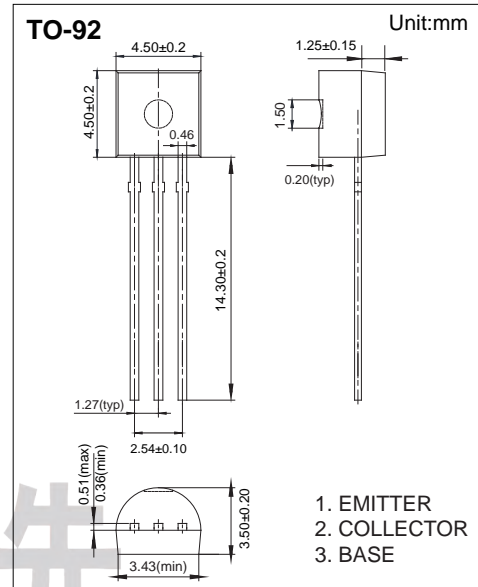


NPN Transistors 2SD882S

■ Features

- High current output up to 3A
- Low saturation voltage
- Complement to 2SB772S



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	40	V
Collector - Emitter Voltage	V_{CEO}	30	
Emitter - Base Voltage	V_{EBO}	5	
Collector Current - Continuous	I_C	3	A
Collector Current - Pulse	I_{CP}	7	
Base Current	I_B	0.6	
Collector Power Dissipation	P_C	500	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to 150	

Transistor

NPN Transistors 2SD882S

■ Electrical Characteristics Ta = 25°C

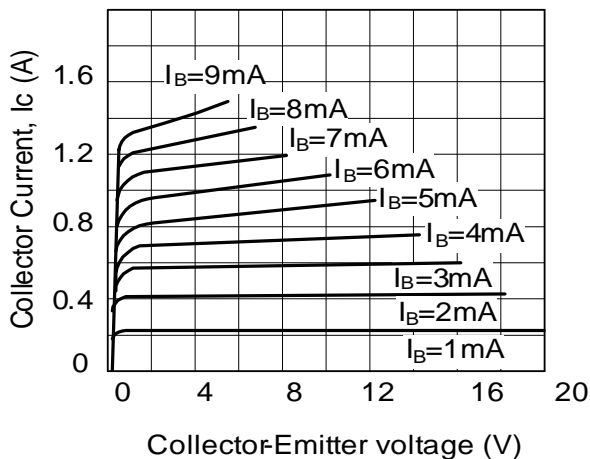
Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _C = 100 μA, I _E =0	40			V
Collector- emitter breakdown voltage	V _{CE0}	I _C = 1 mA, I _B =0	30			
Emitter - base breakdown voltage	V _{EB0}	I _E = 100 μA, I _C =0	5			
Collector cut-off current	I _{CB0}	V _{CB} = 30 V, I _E =0			1	μA
Emitter cut-off current	I _{EB0}	V _{EB} = 3V, I _C =0			1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =2 A, I _B = 200mA			0.5	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C =2 A, I _B = 200mA			2	
DC current gain	h _{FE(1)}	V _{CE} = 2V, I _C = 20mA	30			
	h _{FE(2)}	V _{CE} = 2V, I _C = 1A	100		400	
Output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz		45		pF
Transition frequency	f _T	V _{CE} = 6V, I _C = 20mA, f=30MHz		80		MHz

■ Classification of h_{FE(2)}

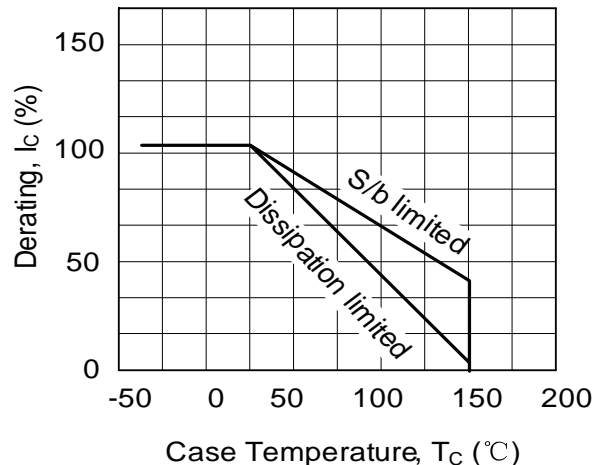
Rank	Q	P	E
Range	100-200	160-320	200-400

■ Typical Characteristics

Static Characteristics



Derating Curve of Safe Operating Areas



Transistor

NPN Transistors 2SD882S

■ Typical Characteristics

